

	L #	Hits	Search Text	DBs	Time Stamp
1	L6	2781	((partially adj cured) or B-stage or pregreg) near8 (polymer\$6 or polyimide or polyimide or epoxy or epoxies)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	2004/12/29 10:23
2	L4	79	(partially adj cured) and (electronic adj package) and polymer\$4	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	2004/12/29 10:23
3	L5	37	L4 and (@ad<"20000213")	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	2004/12/29 10:43
4	L7	53	L6 and (electronic adj package)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	2004/12/29 10:23

	L #	Hits	Search Text	DBs	Time Stamp
5	L8	107	"microelectronic interconnect"	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:24
6	L9	357854	polymeric	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:24
7	L10	265619	(bump or solder)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:24
8	L11	6024	(second! near2 polymeric)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:25

	L #	Hits	Search Text	DBs	Time Stamp
9	L12	2	8 and 10 and 11	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:29
10	L13	1	("2002/0109228").URPN.	USPAT	2004/12/29 10:29
11	L14	42	8 and 10	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:30
12	L15	42	14 and ((@ad<"200100213") or (@rlad<"20010213"))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:43
13	L16	2	8 and 11	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:34

	L #	Hits	Search Text	DBs	Time Stamp
14	L17	2770	(438/106).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:35
15	L24	7951	17 or 18 or 19 or 20 or 21 or 22 or 23	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:38
16	L25	3	24 and 8	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:38
17	L26	493	24 and 9	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:38

	L #	Hits	Search Text	DBs	Time Stamp
18	L29	32	14 and ((@ad<"20010213") or (@rlad<"20010213"))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:43
19	L30	44	L4 and (@ad<"20010213")	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:43
20	L28	370	26 and ((@ad<"20010213") or (@rlad<"20010213"))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 10:43
21	L31	5	("3512051" "4505029" "5143865" "5860585").PN.	US- PGPUB; USPAT; USOCR	2004/12/29 11:11
22	L32	0	("6340630").URPN.	USPAT	2004/12/29 11:11

	L #	Hits	Search Text	DBs	Time Stamp
23	L18	1036	(438/107).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 11:16
24	L19	820	(438/113).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 11:39
25	L20	190	(438/114).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 12:01
26	L21	1319	(438/118).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 12:08

	L #	Hits	Search Text	DBs	Time Stamp
27	L22	2328	(438/612).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 12:59
28	L23	1120	(438/613).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 13:10

US-PAT-NO: 6506681

DOCUMENT-IDENTIFIER: US 6506681 B2
See image for Certificate of Correction

TITLE: Thin flip--chip method

----- KWIC -----

Application Filing Date - AD (1):
20001206

Detailed Description Text - DETX (4):

As referred to herein, "bumping" comprises a process of adding raised electrically conductive contacts or bumps, typically a solder metal alloy, to bond pads formed on the active surface of a semiconductor die formed on the active surface area of a semiconductor wafer. Although electrically conductive bumps 18 (electrically conductive bumps 18 will be described hereafter as "conductive bumps") are preferably formed of various solder alloys, it is understood that any other materials known in the art (e.g., gold, indium, tin, lead, silver or alloys thereof) that can serve to make electrical interconnects to the circuits and/or bond pads 16 of wafer 10 can also be used. Additionally, the conductive bumps 18 may be formed of conductive polymeric and epoxy materials and may include various metals being contained therein, may be plated with metals after formation, etc.

Current US Cross Reference Classification - CCXR
(4):
438/113